

Claim 105 should be replaced with:

105. (Amended) The HVFET according to claim 1 wherein the buried region has a doped impurity concentration of approximately  $2 \times 10^{12}/\text{cm}^2$ .

Claim 106 should be replaced with:

106. (Amended) The HVFET according to claim 1 wherein the second conduction channel has a doped impurity concentration of approximately  $2 \times 10^{12}/\text{cm}^2$ .

Claim 110 should be replaced with:

110. (Amended) The HVFET according to claim 12 wherein the buried region has a doped impurity concentration approximately twice that of the one JFET channel.

Claim 111 should be replaced with:

111. (Amended) The HVFET according to claim 12 wherein the buried region has a doped impurity concentration of approximately  $2 \times 10^{12}/\text{cm}^2$ .

Claim 112 should be replaced with:

112. (Amended) The HVFET according to claim 12 wherein the another JFET channel has a doped impurity concentration of approximately  $2 \times 10^{12}/\text{cm}^2$ .

Claim 116 should be replaced with:

116. (Amended) The HVFET according to claim 68 wherein the buried region has a doped impurity concentration approximately twice that of the first region above the buried layer.